

TRS3232E 采用小型封装且具有 ±15kV IEC ESD 保护的 3V 至 5.5V 多通道 RS-232 线路驱动器和接收器

1 特性

- 为 RS-232 总线引脚提供 ESD 保护
 - ±15kV HBM
 - ±8kV (IEC61000-4-2, 接触放电)
 - ±15kV (IEC61000-4-2, 气隙放电)
- 符合或超出 TIA/EIA-232-F 和 ITU V.28 标准的要求
- 由 3V 至 5.5V V_{CC} 电源供电
 - 可与低至 2.7V V_{CC} 的 RS-232 交互操作
- 运行速率高达 250kbps
- 两个驱动器和两个接收器
- 低电源电流：300 μ A (典型值)
- 外部电容器：4 × 0.1 μ F
- 支持 5V 逻辑输入 (3.3V 电源时)
- 采用近似于芯片级封装 (QFN-16, 3mm × 3mm), 比 SOIC-16 小 85%
- 与备选高速器件引脚兼容 (1Mbps)
 - SN65C3232E (-40°C 至 +85°C)
 - SN75C3232E (0°C 至 70°C)

2 应用

- 工业 PC
- 有线网络
- 数据中心和企业级计算
- 电池供电型系统
- 笔记本电脑
- 掌上电脑
- 手持设备

3 说明

TRS3232E 器件由两个线路驱动器、两个线路接收器和一个双电荷泵电路组成，具有引脚对引脚 (串行端口连接引脚，包括 GND) ±15kV IEC ESD 保护。

该器件符合 TIA/EIA-232-F 的要求并在异步通信控制器与串行端口连接器之间提供电气接口。电荷泵和四个小型外部电容器支持由单个 3V 至 5.5V 电源供电。这些器件以高达 250kbps 的数据信号传输速率和最高 30V/ μ s 的驱动器输出压摆率运行。

封装信息

器件型号	封装 ⁽¹⁾	封装尺寸 ⁽²⁾
TRS3232E	SOIC (D, 16)	9.9mm × 6mm
	SSOP (DB, 16)	6.2mm × 7.8mm
	SOIC (DW, 16)	10.3mm × 10.3mm
	TSSOP (PW, 16)	5mm × 6.4mm
	VQFN (RGT, 16)	3mm × 3mm
	SOT-23-THN (DYY, 16)	4.2mm × 2mm

(1) 有关更多信息，请参阅节 11。

(2) 封装尺寸 (长 × 宽) 为标称值，并包括引脚 (如适用)。

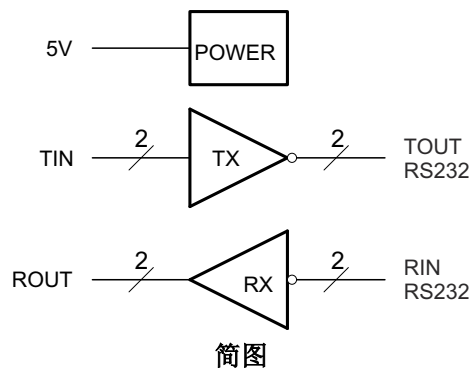


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4 Pin Configuration and Functions

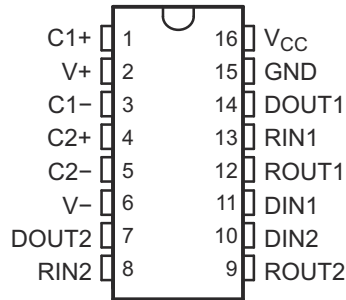


图 4-1. DB, PW or DYY Package
16-Pin SSOP, TSSOP, or SOT-23-THN
(Top View)

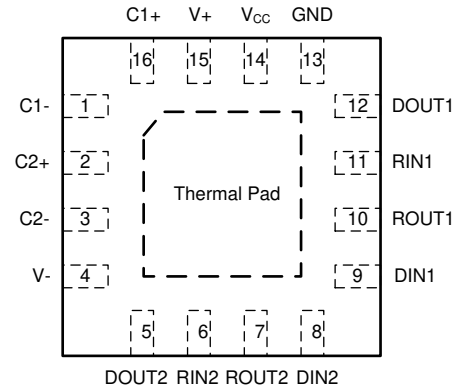


图 4-2. RGT package, 16 Pin VQFN, Top View

表 4-1. Pin Functions

PIN		RGT	TYPE	DESCRIPTION
NAME	NO.			
C1+	1	16	—	Positive lead of C1 capacitor
C1-	3	1	—	Negative lead of C1 capacitor
C2+	4	2	—	Positive lead of C2 capacitor
C2-	5	3	—	Negative lead of C2 capacitor
DIN1	11	9	I	Logic data input (from UART)
DIN2	10	8	I	Logic data input (from UART)
DOUT2	7	5	O	RS232 line data output (to remote RS232 system)
DOUT1	14	12	O	RS232 line data output (to remote RS232 system)
GND	15	13	—	Ground
RIN1	13	11	I	RS232 line data input (from remote RS232 system)
RIN2	8	6	I	RS232 line data input (from remote RS232 system)
ROUT2	9	7	O	Logic data output (to UART)
ROUT1	12	10	O	Logic data output (to UART)
V+	2	15	O	Positive charge pump output for storage capacitor only
V-	6	4	O	Negative charge pump output for storage capacitor only
V _{CC}	16	14	—	Supply voltage, connect to external 3-V to 5.5-V power supply
Thermal Pad		Yes	—	Thermal pad for improving heat dissipation. Can be connected to GND or left floating.

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT	
V _{CC}	Supply voltage ⁽²⁾	- 0.3	6	V	
V+	Positive output supply voltage ⁽²⁾	- 0.3	7	V	
V-	Negative output supply voltage ⁽²⁾	0.3	- 7	V	
V+ - V-	Supply voltage difference ⁽²⁾		13	V	
V _I	Input voltage	Drivers	- 0.3	6	V
		Receivers	- 25	25	V
V _O	Output voltage	Drivers	- 13.2	13.2	V
		Receivers	- 0.3	V _{CC} + 0.3	V
T _J	Operating virtual junction temperature		150	°C	
T _{stg}	Storage temperature	- 65	150	°C	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to network GND.

5.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±2000	V
			±15000	
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 ESD Ratings - IEC Specifications

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	IEC 61000-4-2, Contact Discharge ⁽¹⁾	±8000	V
		IEC 61000-4-2, Air-Gap Discharge ⁽¹⁾	±15000	

- (1) For RGT, D, DB and PW packages only: Minimum of 1-μF capacitor between VCC and GND is required to meet the specified IEC 61000-4-2 rating.
- (2) For optimized IEC ESD performance for DYY package, the recommendation is to have series resistor ($\geq 50\Omega$), on all logic inputs directly connected to power or ground, to minimize the transient currents going into or out of the logic pins.

5.4 Recommended Operating Conditions

See [图 8-1](#).⁽¹⁾

			MIN	NOM	MAX	UNIT
Supply voltage		$V_{CC} = 3.3\text{ V}$	3	3.3	3.6	V
		$V_{CC} = 5\text{ V}$	4.5	5	5.5	
V_{IH} Driver high-level input voltage	DIN	$V_{CC} = 3.3\text{ V}$	2		5.5	V
		$V_{CC} = 5\text{ V}$	2.4		5.5	
V_{IL} Driver low-level input voltage	DIN		0		0.8	V
V_I Receiver input voltage	RIN		- 25		25	V
T_A Operating free-air temperature	TRS3232EC		0		70	°C
	TRS3232EI		- 40		85	

(1) $C_1 - C_4 = 0.1\ \mu\text{F}$ at $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$; $C_1 = 0.047\ \mu\text{F}$, $C_2 - C_4 = 0.33\ \mu\text{F}$ at $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$.

5.5 Thermal Information

THERMAL METRIC ⁽¹⁾	TRS3232E						UNIT
	PW (TSSOP)	D (SOIC)	DW (SOIC)	DB (SSOP)	RGT (VQFN)	DYY (SOT-23-THN)	
	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$ Junction-to-ambient thermal resistance	108.2	85.9	72.3	103.1	48.8	106.2	°C/W
$R_{\theta JCTop}$ Junction-to-case (top) thermal resistance	39.0	43.1	33.5	49.2	55.8	47.4	°C/W
$R_{\theta JB}$ Junction-to-board thermal resistance	54.4	44.5	37.1	54.8	23.2	44.7	°C/W
ψ_{JT} Junction-to-top characterization parameter	3.3	10.1	7.5	12.0	1.7	1.7	°C/W
ψ_{JB} Junction-to-board characterization parameter	53.8	44.1	37.1	54.1	23.2	43.7	°C/W
$R_{\theta JCbot}$ Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	9.0	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

5.6 Electrical Characteristics — Device

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 图 8-1).⁽¹⁾

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
I _{CC}	Supply current	No load, V _{CC} = 3.3 V or 5 V		0.3	1	mA

- (1) Test conditions are C1 - C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 - C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.
- (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

5.7 Electrical Characteristics — Driver

over operating free-air temperature range (unless otherwise noted) (see 图 8-1).⁽¹⁾

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V _{OH}	High-level output voltage	DOUT at R _L = 3 kΩ to GND, DIN = GND	5	5.4		V
V _{OL}	Low-level output voltage	DOUT at R _L = 3 kΩ to GND, DIN = V _{CC}	- 5	- 5.4		V
I _{IH}	High-level input current	V _I = V _{CC}		±0.01	±1	μA
I _{IL}	Low-level input current	V _I at GND		±0.01	±1	μA
I _{OS} ⁽³⁾	Short-circuit output current	V _{CC} = 3.6 V, V _O = 0 V		±35	±60	mA
		V _{CC} = 5.5 V, V _O = 0 V				
r _O	Output resistance	V _{CC} , V+, and V- = 0 V, V _O = ±2 V	300	10M		Ω

- (1) Test conditions are C1 - C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 - C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.
- (2) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.
- (3) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

5.8 Electrical Characteristics — Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see [图 8-1](#)).⁽²⁾

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = -1 mA	V _{CC} - 0.6	V _{CC} - 0.1		V
V _{OL}	Low-level output voltage	I _{OL} = 1.6 mA			0.4	V
V _{IT+}	Positive-going input threshold voltage	V _{CC} = 3.3 V		1.5	2.4	V
		V _{CC} = 5 V		1.8	2.4	
V _{IT-}	Negative-going input threshold voltage	V _{CC} = 3.3 V	0.6	1.2		V
		V _{CC} = 5 V	0.8	1.5		
V _{hys}	Input hysteresis (V _{IT+} - V _{IT-})			0.3		V
r _i	Input resistance	V _I = ±3 V to ±25 V	3	5	7	kΩ

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(2) Test conditions are C1 - C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 - C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

5.9 Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see [图 8-1](#)).⁽¹⁾

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
Maximum data rate		R _L = 3 kΩ, C _L = 1000 pF, see 图 6-1 One DOUT switching,	RGT package	250	500	kbps
		D, DB, DW and PW packages		150	250	
t _{sk(p)}	Driver pulse skew ⁽³⁾	R _L = 3 kΩ, C _L = 1000 pF, V _{CC} = 5 V 图 6-2	RGT package		50	ns
		R _L = 3 kΩ to 7 kΩ, C _L = 150 pF to 2500 pF see 图 6-2	D, DB, DW and PW packages		300	
SR(tr)	Driver slew rate, transition region (see 图 6-1)	R _L = 3 kΩ to 7 kΩ, V _{CC} = 3.3 V	C _L = 150 pF to 1000 pF	6	30	V/μs
			C _L = 150 pF to 2500 pF	4	30	
t _{PLH}	Receiver propagation delay time, low- to high-level output	C _L = 150 pF, see 图 6-3	RGT package		90	ns
			D, DB, DW and PW packages		300	
t _{PHL}	Receiver propagation delay time, high- to low-level output	C _L = 150 pF, see 图 6-3	RGT package		100	ns
			D, DB, DW and PW packages		300	
t _{sk(p)}	Receiver pulse skew ⁽³⁾		RGT package		20	ns
			D, DB, DW and PW packages		300	

(1) Test conditions are C1 - C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 - C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(3) Pulse skew is defined as |t_{PLH} - t_{PHL}| of each channel of the same device.

Typical Characteristics

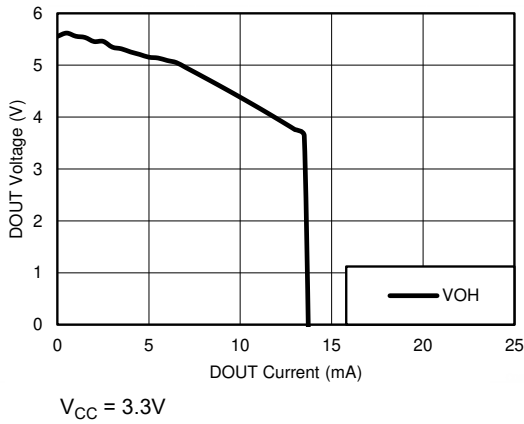


图 5-1. DOUT V_{OH} vs Load Current, Both Drivers Loaded

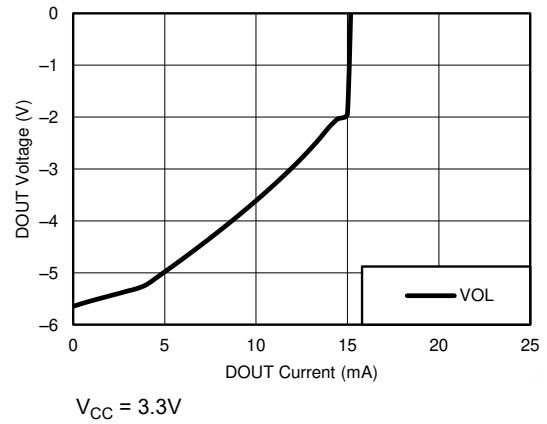


图 5-2. DOUT V_{OL} vs Load Current, Both Drivers Loaded

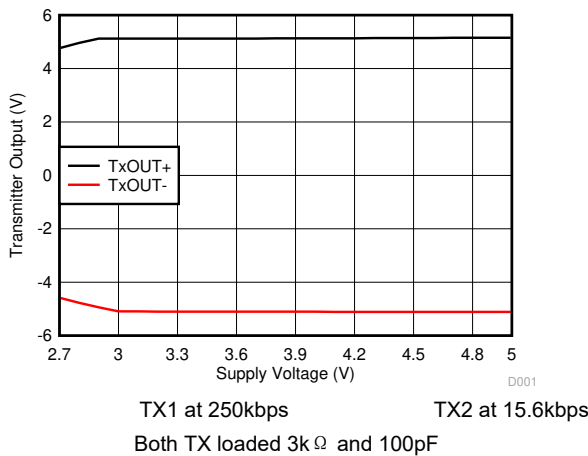


图 5-3. Driver Output Voltage vs. Supply Voltage, Both Drivers Loaded

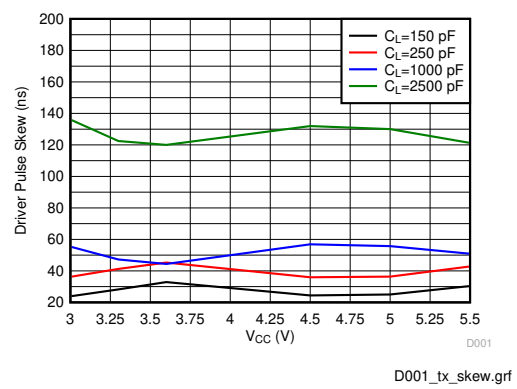


图 5-4. Driver Pulse Skew (RGT Package)

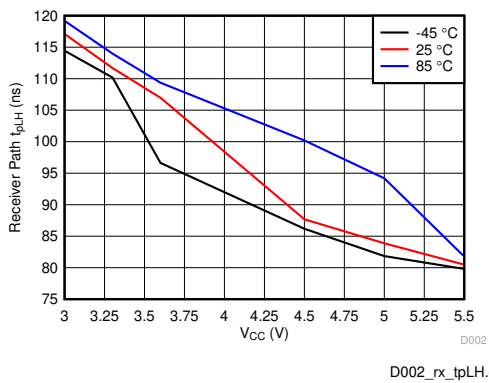


图 5-5. Receiver Path Low-to-High Propagation Delay (RGT Package)

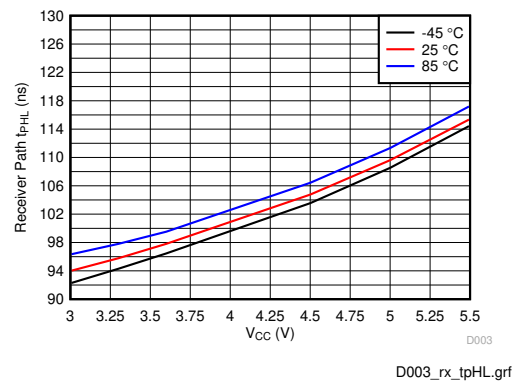


图 5-6. Receiver Path High-to-Low Propagation Delay (RGT Package)

Typical Characteristics

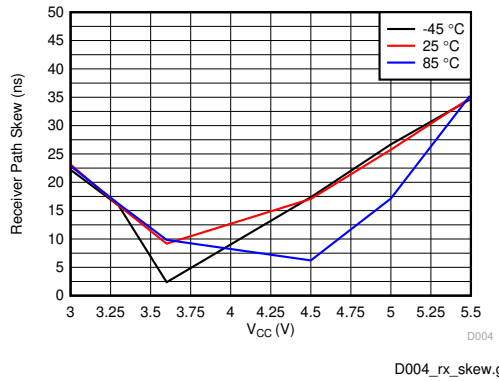
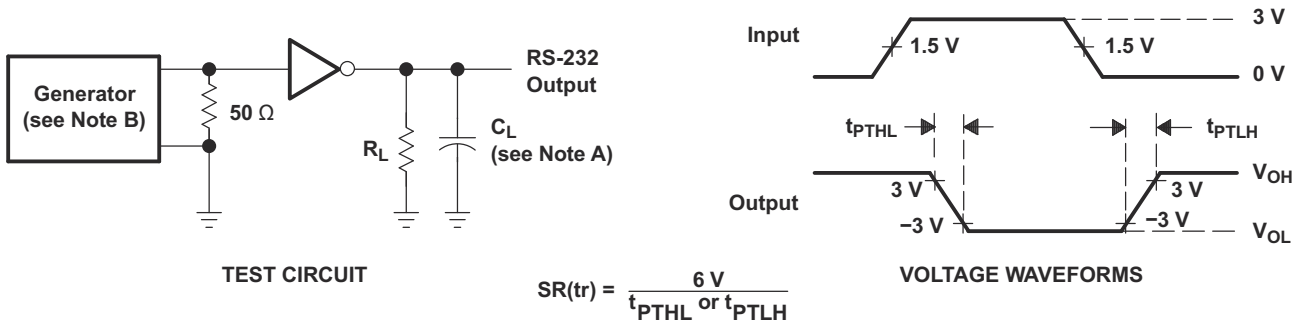


图 5-7. Receiver Path Skew ($|t_{pHL} - t_{pLH}|$) (RGT Package)

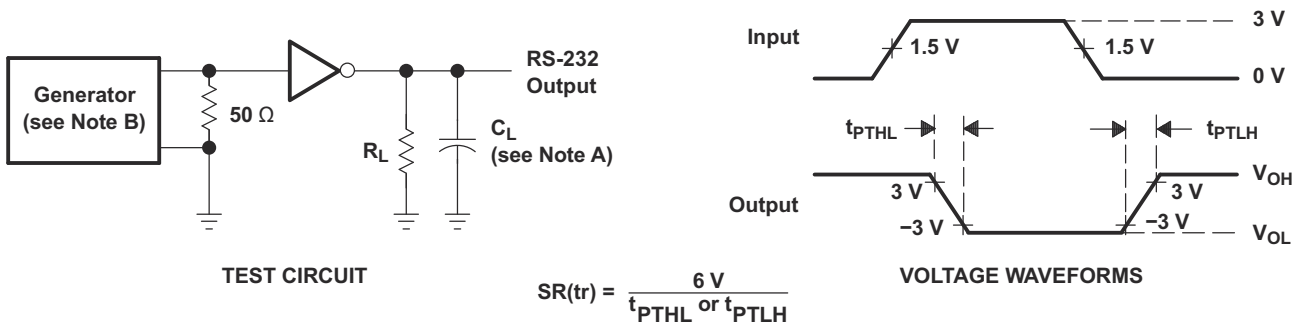
6 Parameter Measurement Information



A. C_L includes probe and jig capacitance

B. The pulse generator has the following characteristics: PRR = 250 kbps, $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$

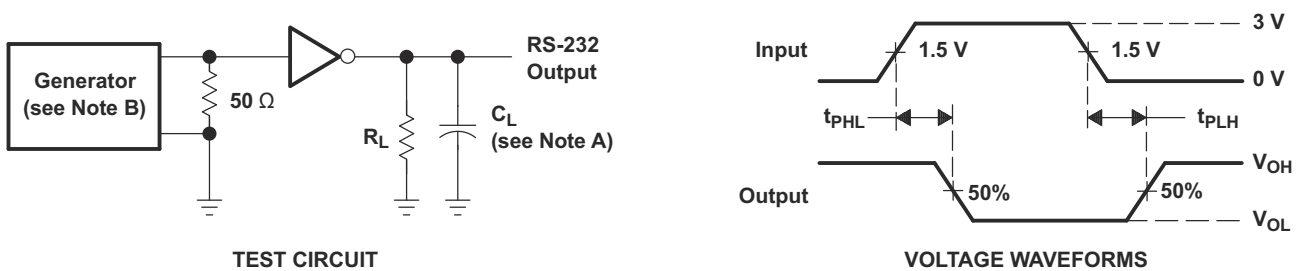
图 6-1. Driver Slew Rate



A. C_L includes probe and jig capacitance

B. The pulse generator has the following characteristics: PRR = 250 kbps, $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$

图 6-2. Driver Pulse Skew



A. C_L includes probe and jig capacitance

B. The pulse generator has the following characteristics: $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$

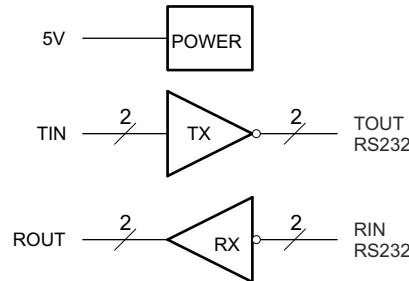
图 6-3. Receiver Propagation Delay Times

7 Detailed Description

7.1 Overview

The TRS3232E device consists of two line drivers, two-line receivers, and a dual charge-pump circuit with IEC61000-4-2 ESD protection terminal to terminal (serial-port connection terminals, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3V to 5.5V supply. The device operates at data signaling rates up to 250kbps and a maximum of 30V/μs driver output slew rate. Outputs are protected against shorts to ground.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Power

The power block increases, inverts, and regulates voltage at V+ and V- pins using a charge pump that requires four external capacitors.

7.3.2 RS232 Driver

Two drivers interface standard logic level to RS232 levels. Both DIN inputs must be valid high or low.

7.3.3 RS232 Receiver

Two receivers interface RS232 levels to standard logic levels. An open input will result in a high output on ROUT. Each RIN input includes an internal standard RS232 load.

7.4 Device Functional Modes

表 7-1 和 表 7-2 list the functional modes of the drivers and receivers of TRS3232E.

表 7-1. Each Driver ⁽¹⁾

INPUT DIN	OUTPUT DOUT
L	H
H	L

(1) H = high level, L = low level

表 7-2. Each Receiver ⁽¹⁾

INPUT RIN	OUTPUT ROUT
L	H
H	L
Open	H

(1) H = high level, L = low level,
Open = input disconnected or connected driver off

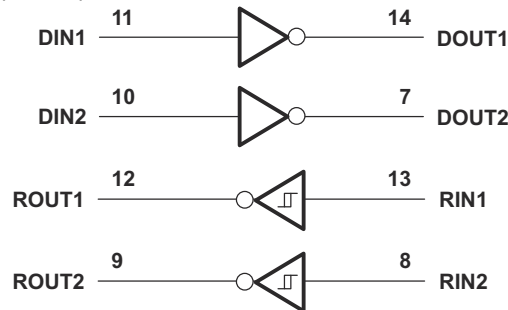


图 7-1. Logic Diagram

7.4.1 V_{CC} Powered by 3V to 5.5V

The device is in normal operation.

7.4.2 V_{CC} Unpowered, $V_{CC} = 0V$

When TRS3232E is unpowered, it can be safely connected to an active remote RS232 device.

8 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

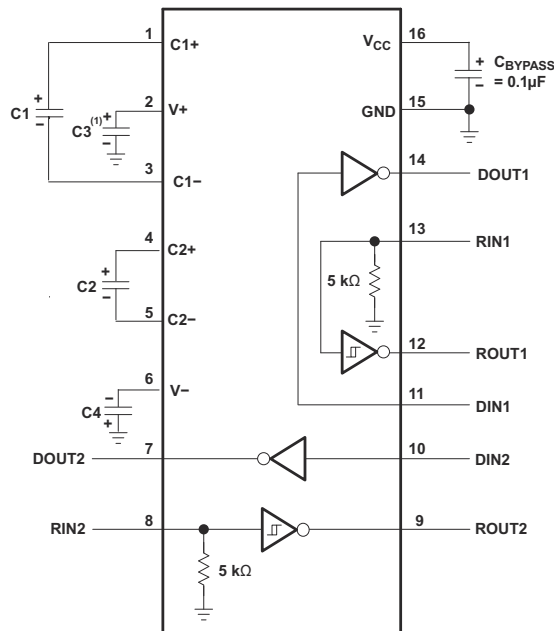
8.1 Application Information

The TRS3232E interfaces logic lines from a UART or microcontroller to the voltage and current levels needed for RS232 communication. The TIN inputs will accept 5V logic with 3.3V V_{CC} supply. All baud rates up to 250kbps are supported.

It is important to use the correct capacitors for the V_{CC} voltage. This will reduce ripple voltage on the TOUT outputs. If only one driver is needed, the unused driver input should be connected to V_{CC} or ground.

8.2 Typical Application

ROUT and DIN connect to UART or general-purpose logic lines. RIN and DOUT lines connect to a RS232 connector or cable. For proper operation, add capacitors as shown in 表 8-1.



A. C3 can be connected to V_{CC} or GND

Resistor values shown are nominal.

Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

图 8-1. Typical Operating Circuit and Capacitor Values

表 8-1. V_{CC} vs Capacitor Values

V_{CC}	C1	C2, C3, C4
3.3V ± 0.3V	0.1μF	0.1μF
5V ± 0.5V	0.047μF	0.33μF
3V ± 5.5V	0.1μF	0.47μF

8.2.1 Design Requirements

The recommended V_{CC} is 3.3V or 5V. 3V to 5.5V is also possible.

The maximum recommended bit rate is 250kbps.

8.2.2 Detailed Design Procedure

All DIN inputs must be connected to valid low or high logic levels.

Select capacitor values based on V_{CC} level for best performance.

8.2.3 Application Curve

图 8-2 curves are for 3.3V V_{CC} and 250kbps alternative bit data stream.

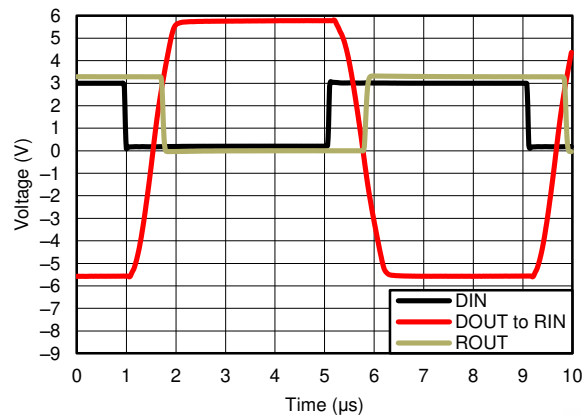


图 8-2. 250kbps Driver to Receiver Loopback Timing Waveform, $V_{CC}= 3.3V$

8.3 Power Supply Recommendations

The supply voltage, V_{CC} , should be between 3V and 5.5V. Select the values of the charge-pump capacitors using 表 8-1.

8.4 Layout

8.4.1 Layout Guidelines

Keep the external capacitor traces short, specifically on the C1 and C2 nodes that have the fastest rise and fall times.

8.4.2 Layout Example

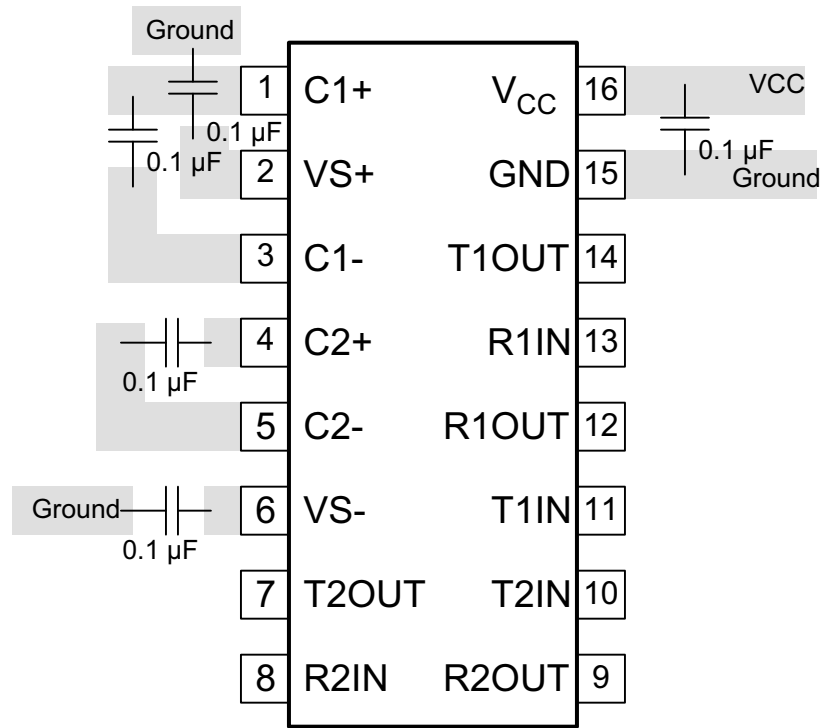


图 8-3. Layout Diagram

9 Device and Documentation Support

9.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 [通知](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

9.2 支持资源

[TI E2E™ 中文支持论坛](#) 是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [使用条款](#)。

9.3 商标

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

9.4 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

9.5 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

10 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision D (June 2021) to Revision E (December 2024)	Page
• 将 <i>器件信息</i> 表更改为 <i>封装信息</i> 表.....	1
• 向数据表中添加了 SOT-23-THN (DYY) 封装.....	1
• Added Note 2 to the <i>ESD ratings - IEC Specifications</i>	4

Changes from Revision C (June 2021) to Revision D (June 2021)	Page
• 添加了 <i>应用工业 PC、有线网络、数据中心和企业级计算</i>	1
• Changed the table note in the <i>ESD Ratings - IEC Specifications</i> to make it applicable to D, DB and PW packages.	4
• Changed the thermal parameter values for D, DB and PW packages in the <i>Thermal Information</i> table.....	5

Changes from Revision B (October 2017) to Revision C (June 2021)	Page
• 向 <i>器件信息</i> 添加了 RGT 封装.....	1
• Added the <i>RGT Pin Configuration</i>	3
• Added the <i>ESD Ratings - IEC Specifications</i>	4
• Added RGT to the <i>Thermal Information</i>	5
• Added RGT package to the <i>Switching Characteristics</i>	7
• Changed the capacitor value From: 1 µf To: 0.1 µf in the <i>Layout Diagram</i>	15

Changes from Revision A (July 2015) to Revision B (October 2017)	Page
• 添加了特性：可与低至 2.7V V _{CC} 的 RS-232 交互操作.....	1
• Added 图 5-3	8

Changes from Revision * (April 2007) to Revision A (July 2015)	Page
• 删除了 <i>订购信息表</i>	1
• 添加了 <i>器件信息表、引脚配置和功能部分、ESD 等级表、热性能信息表、特性说明部分、器件功能模式、应用和实施部分、电源相关建议部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分</i>	1

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TRS3232ECDR	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TRS3232EC
TRS3232ECDR.A	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TRS3232EC
TRS3232ECDW	Obsolete	Production	SOIC (DW) 16	-	-	Call TI	Call TI	0 to 70	TRS3232EC
TRS3232ECDWR	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TRS3232EC
TRS3232ECDWR.B	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TRS3232EC
TRS3232ECPWR	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	0 to 70	RS32EC
TRS3232ECPWR.A	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	RS32EC
TRS3232EIDBR	Active	Production	SSOP (DB) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RS32EI
TRS3232EIDBR.A	Active	Production	SSOP (DB) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RS32EI
TRS3232EIDR	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS3232EI
TRS3232EIDR.A	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS3232EI
TRS3232EIDRG4	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS3232EI
TRS3232EIDRG4.A	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS3232EI
TRS3232EIDW	Obsolete	Production	SOIC (DW) 16	-	-	Call TI	Call TI	-40 to 85	TRS3232EI
TRS3232EIDWR	Obsolete	Production	SOIC (DW) 16	-	-	Call TI	Call TI	-40 to 85	TRS3232EI
TRS3232EIDYYR	Active	Production	SOT-23-THIN (DYY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RS32EI
TRS3232EIDYYR.A	Active	Production	SOT-23-THIN (DYY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RS32EI
TRS3232EIPWR	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RS32EI
TRS3232EIPWR.A	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RS32EI
TRS3232EIPWRG4	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RS32EI
TRS3232EIRGTR	Active	Production	VQFN (RGT) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	3232
TRS3232EIRGTR.A	Active	Production	VQFN (RGT) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	3232

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TRS3232E :

- Automotive : [TRS3232E-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TRS3232ECDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TRS3232ECDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
TRS3232ECPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TRS3232EIDBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
TRS3232EIDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TRS3232EIDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TRS3232EIDRG4	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TRS3232EIDYYR	SOT-23-THIN	DYY	16	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3
TRS3232EIPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TRS3232EIRGTR	VQFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

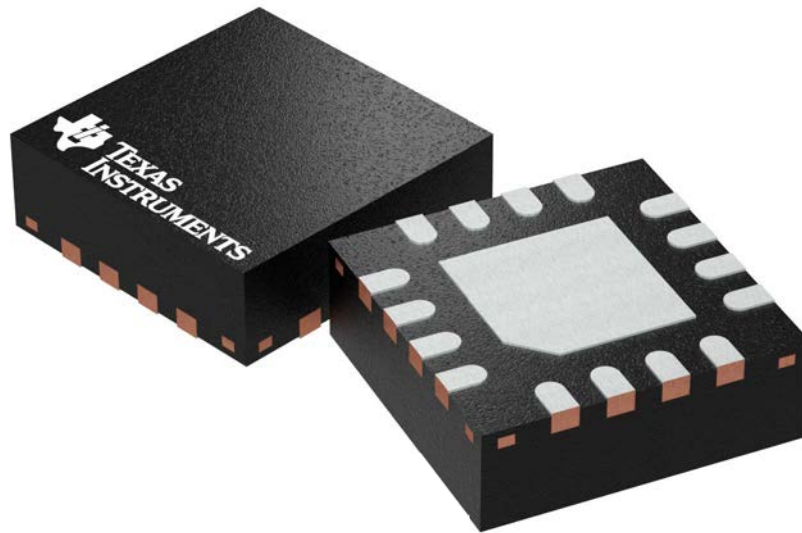
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TRS3232ECDR	SOIC	D	16	2500	353.0	353.0	32.0
TRS3232ECDWR	SOIC	DW	16	2000	350.0	350.0	43.0
TRS3232ECPWR	TSSOP	PW	16	2000	356.0	356.0	35.0
TRS3232EIDBR	SSOP	DB	16	2000	353.0	353.0	32.0
TRS3232EIDR	SOIC	D	16	2500	353.0	353.0	32.0
TRS3232EIDR	SOIC	D	16	2500	353.0	353.0	32.0
TRS3232EIDRG4	SOIC	D	16	2500	353.0	353.0	32.0
TRS3232EIDYYR	SOT-23-THIN	DYY	16	3000	336.6	336.6	31.8
TRS3232EIPWR	TSSOP	PW	16	2000	353.0	353.0	32.0
TRS3232EIRGTR	VQFN	RGT	16	3000	367.0	367.0	35.0

RGT 16

GENERIC PACKAGE VIEW

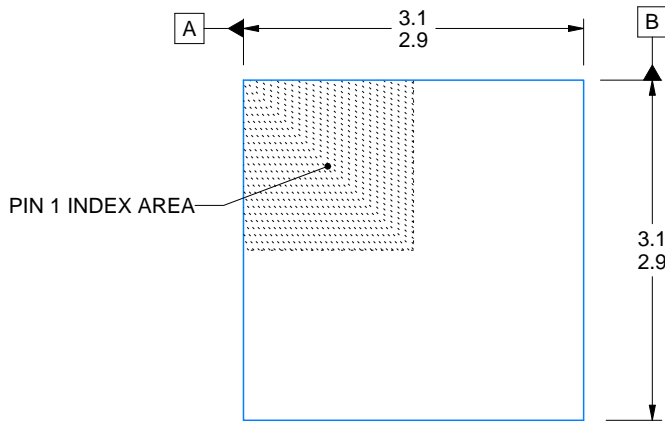
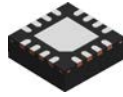
VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

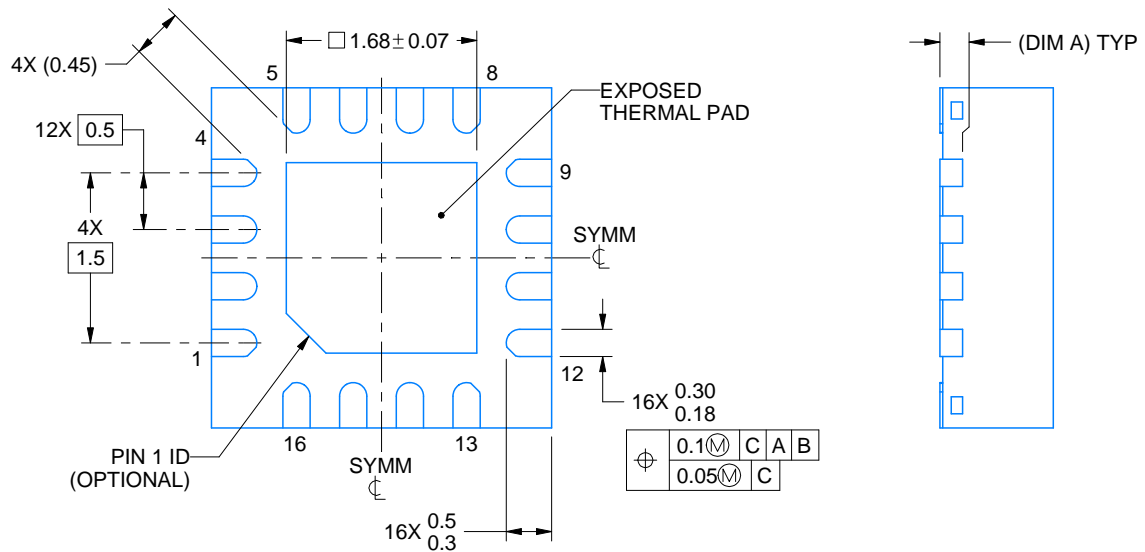
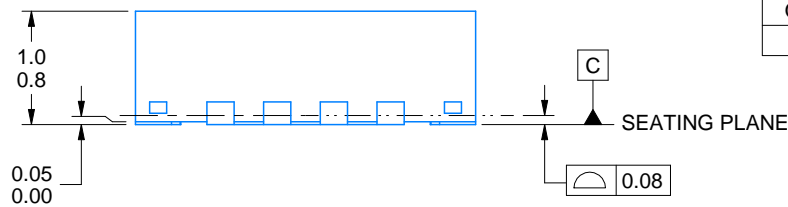


Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4203495/1



SIDE WALL METAL THICKNESS DIM A	
OPTION 1	OPTION 2
0.1	0.2



4222419/E 07/2025

NOTES:

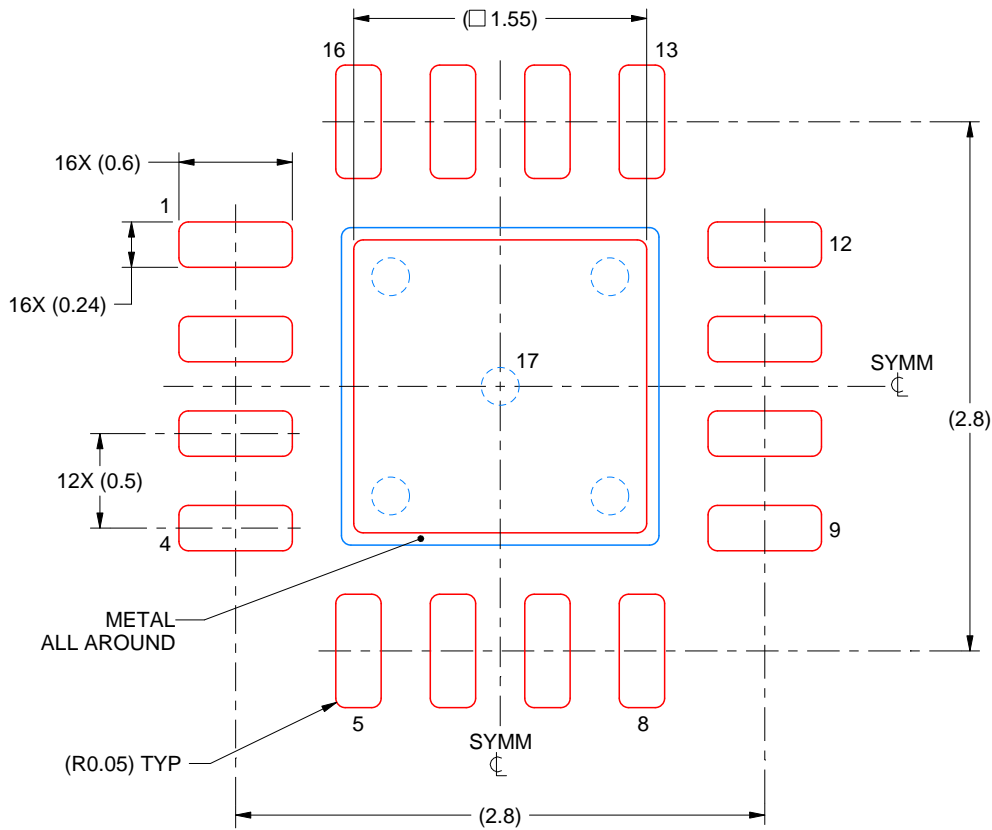
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE STENCIL DESIGN

RGT0016C

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 17:
85% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:25X

4222419/E 07/2025

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AC.

DB0016A



PACKAGE OUTLINE

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



4220763/A 05/2022

NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
- Reference JEDEC registration MO-150.

EXAMPLE BOARD LAYOUT

DB0016A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220763/A 05/2022

NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DB0016A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE

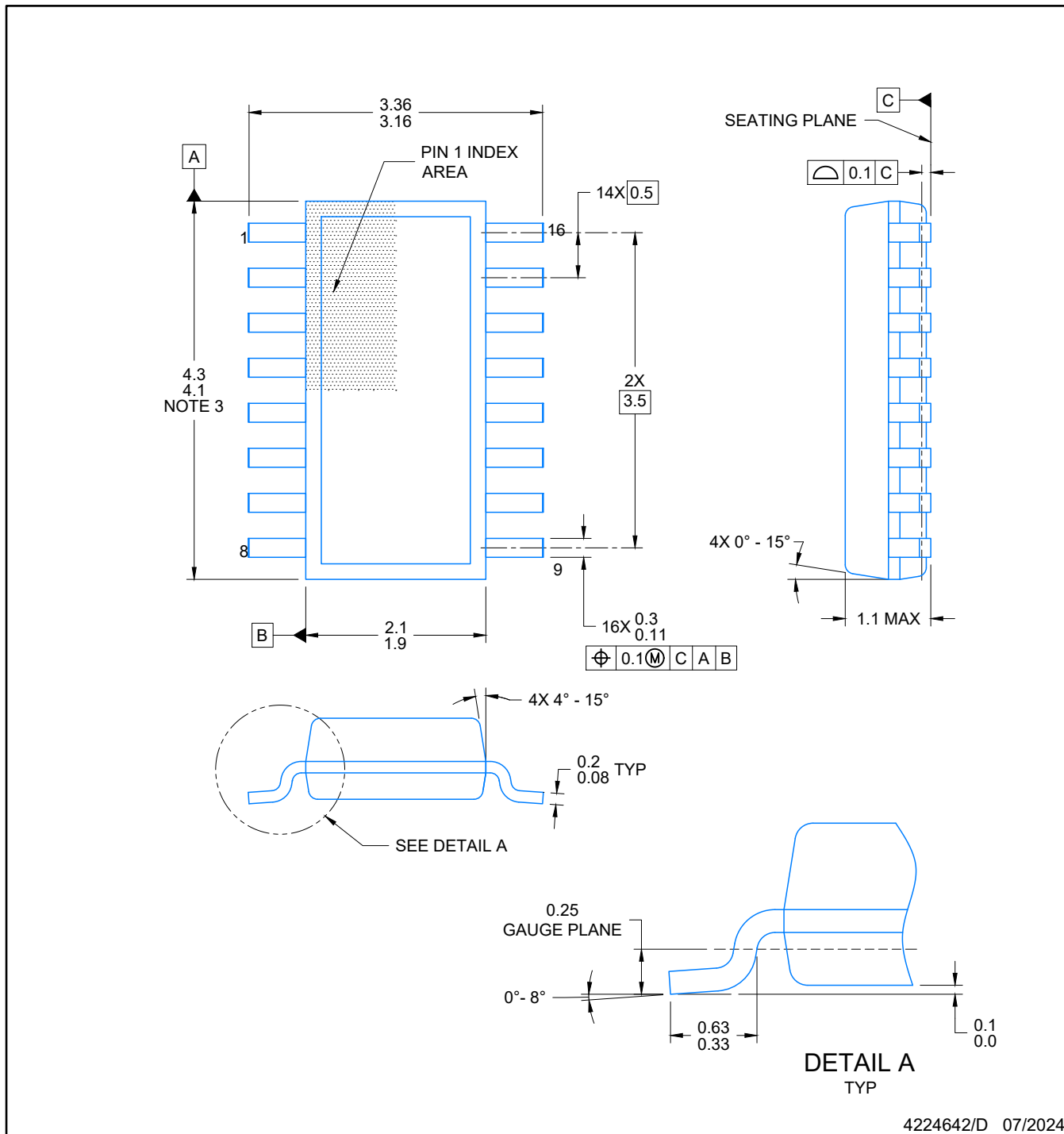


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220763/A 05/2022

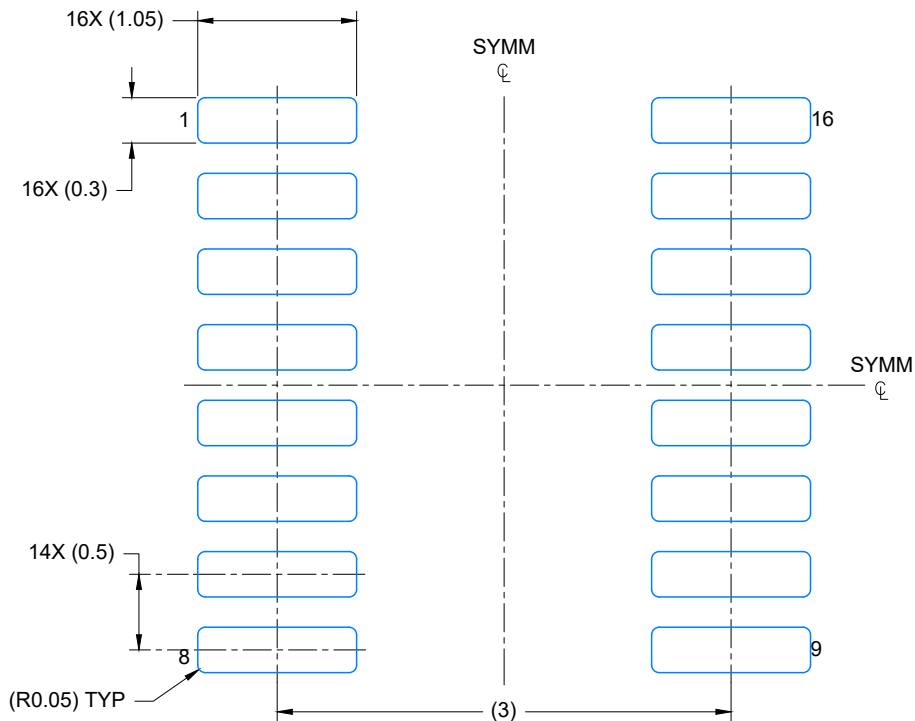
NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

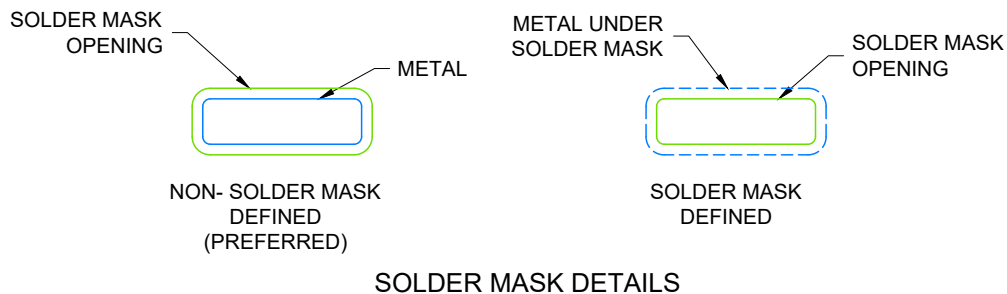


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
5. Reference JEDEC Registration MO-345, Variation AA



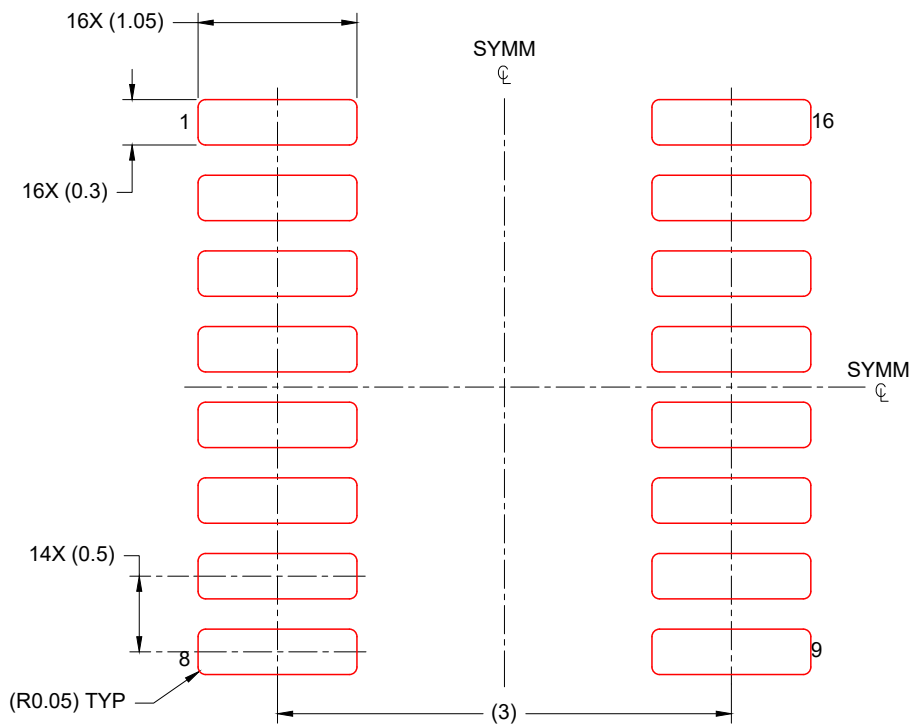
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



4224642/D 07/2024

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 20X

4224642/D 07/2024

NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

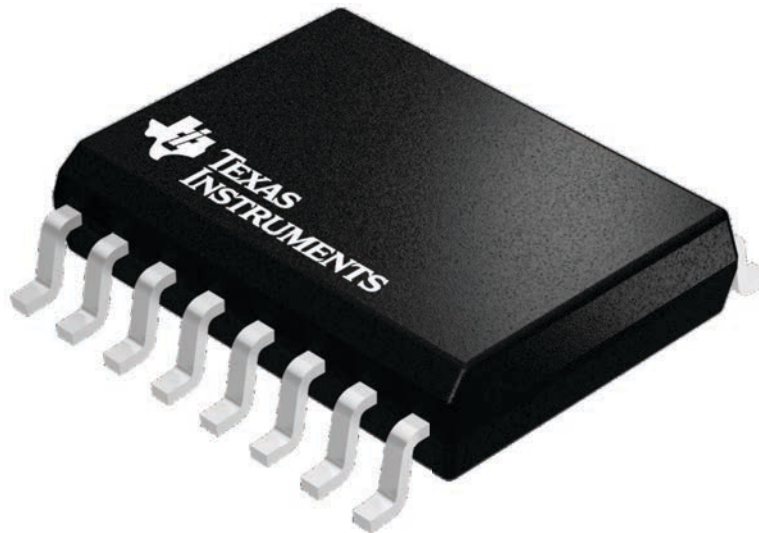
DW 16

SOIC - 2.65 mm max height

7.5 x 10.3, 1.27 mm pitch

SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



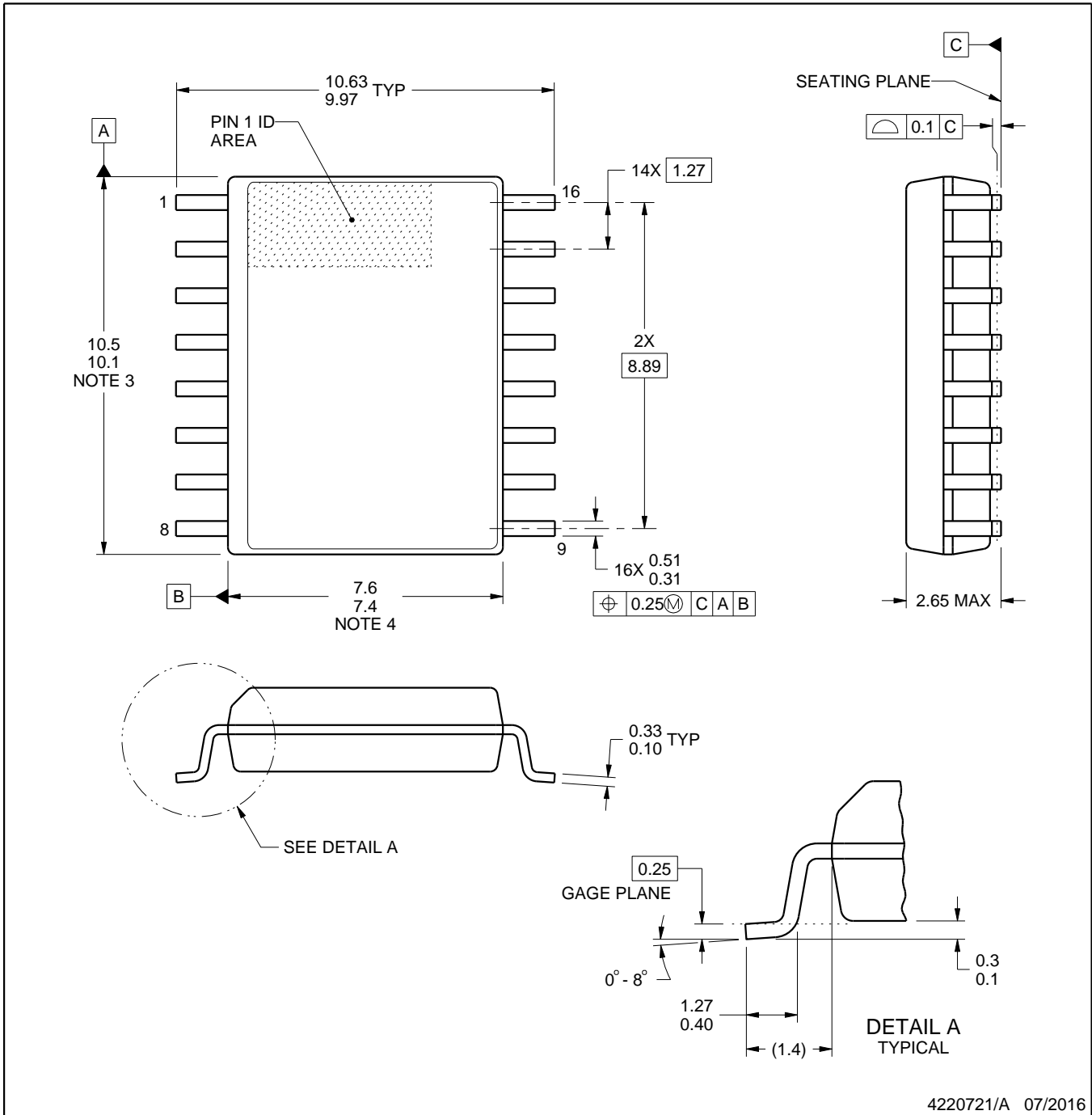
4224780/A



DW0016A

PACKAGE OUTLINE SOIC - 2.65 mm max height

SOIC



4220721/A 07/2016

NOTES:

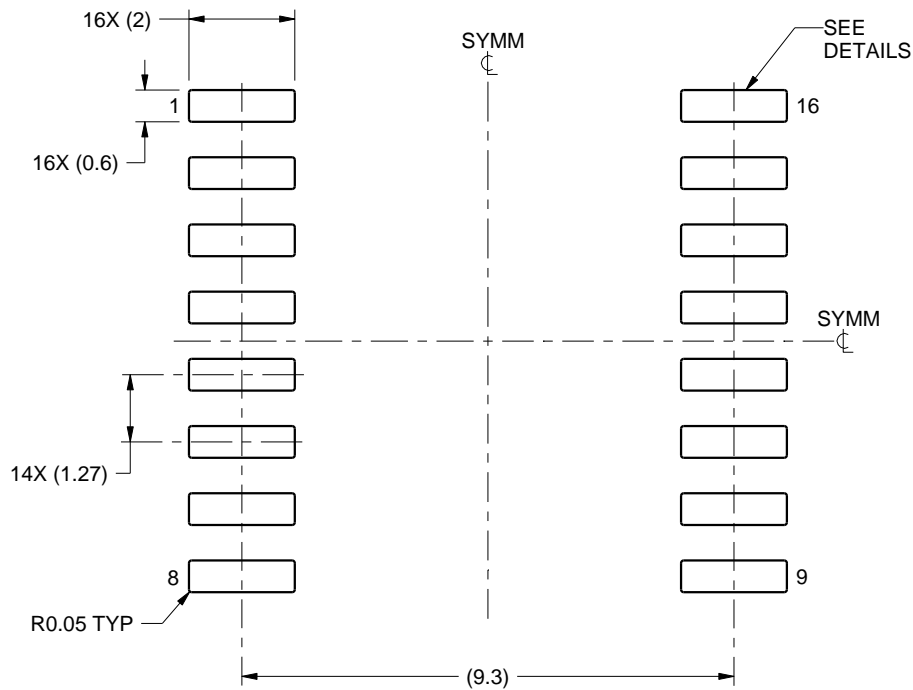
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

DW0016A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE
SCALE:7X



SOLDER MASK DETAILS

4220721/A 07/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0016A

SOIC - 2.65 mm max height

SOIC

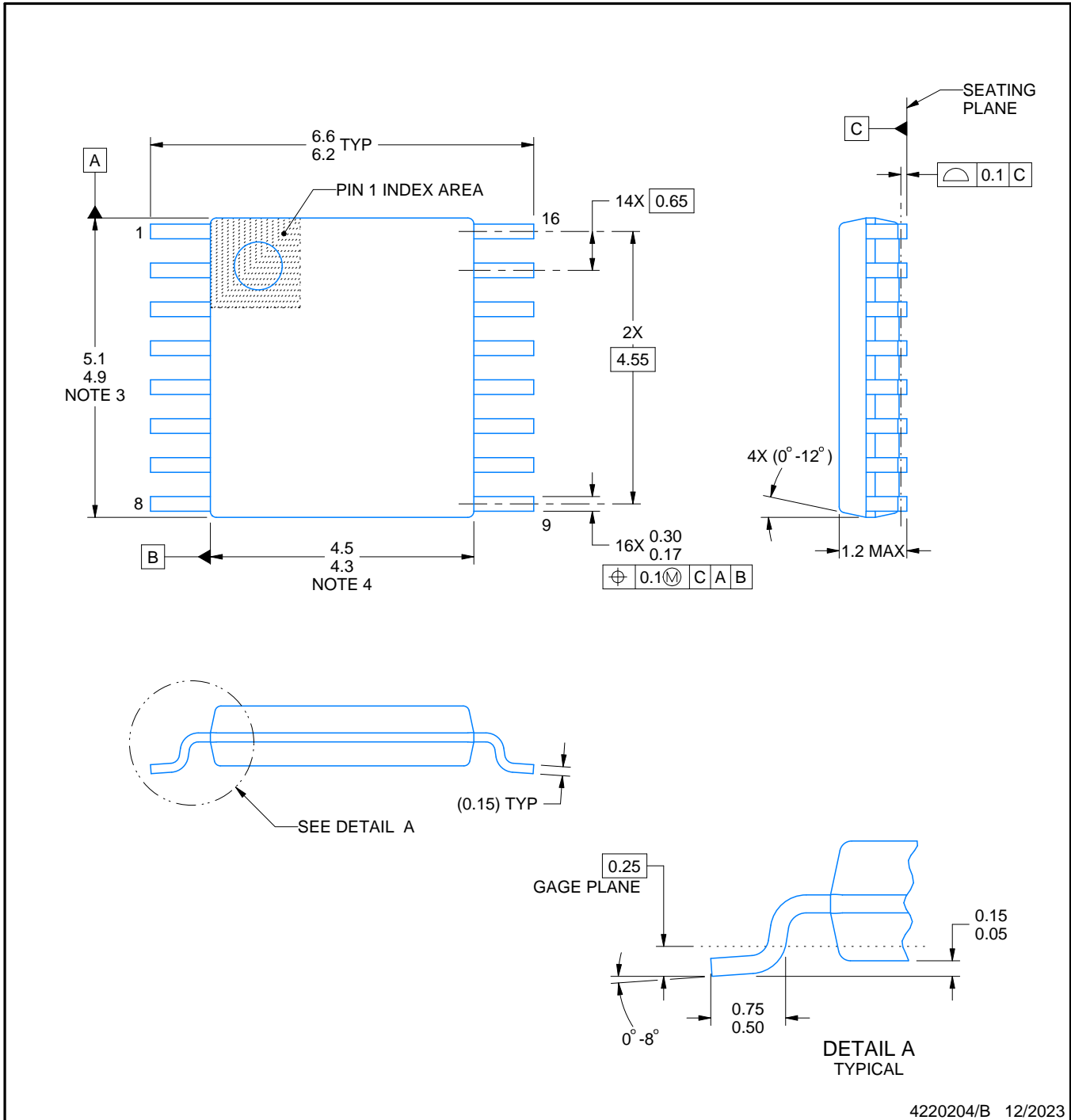


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:7X

4220721/A 07/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



4220204/B 12/2023

NOTES:

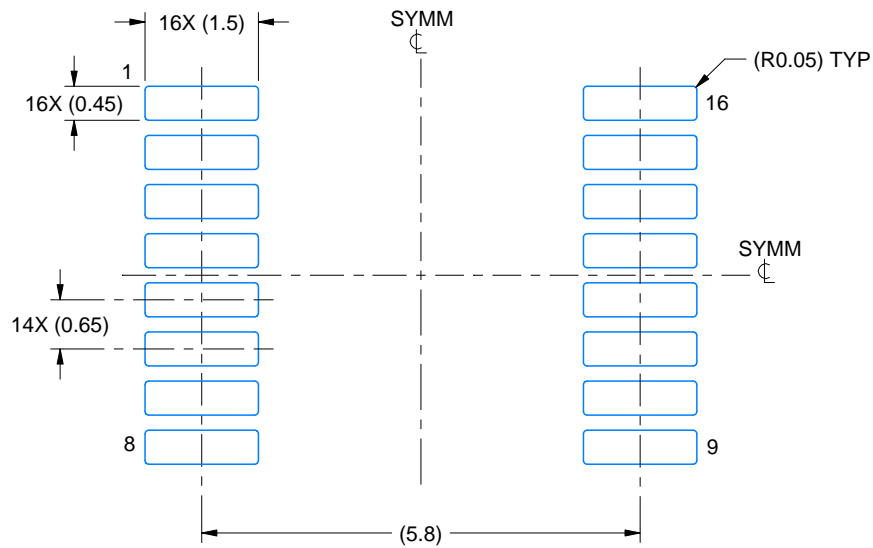
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

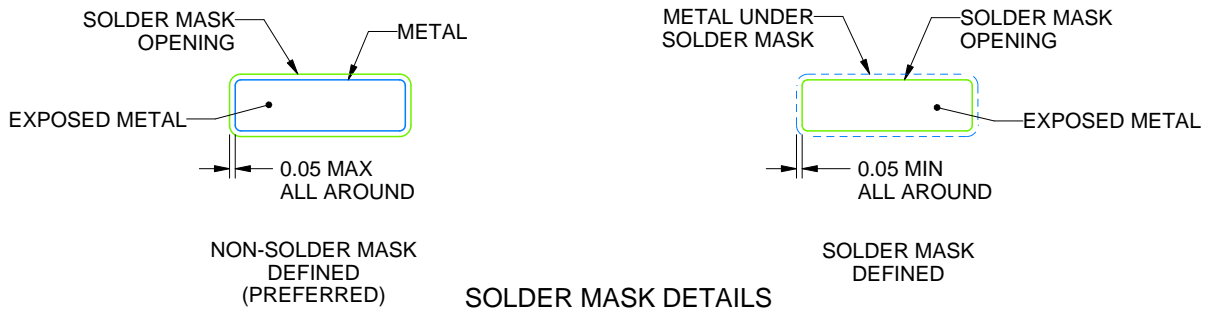
PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220204/B 12/2023

NOTES: (continued)

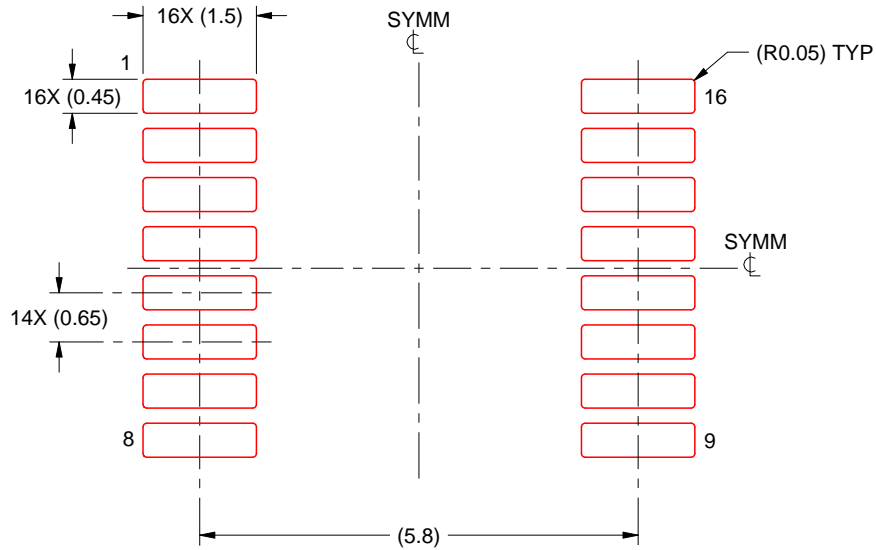
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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